



Bipolar NPN Bare Die – BTN6076

Part Description

The BTN6076 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 160V
- VCEO = 140V
- VEBO = 5V
- hFE = 100-300 @ VCE = 10V, IC = 0.15A
- VCE(Sat) = 0.7V @ IC = 0.15A, IB = 15mA
- fT = 100 MHz @ VCE = 10V, IE = 0A
- COBO = 15pF @ VCB = 10V

Features

Low VCE(sat). Designed to provide performance equivalent to 2N5551

Die Size (Unsawn)

660µm X 660µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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